

Silicon NPN Darlington Power Transistor

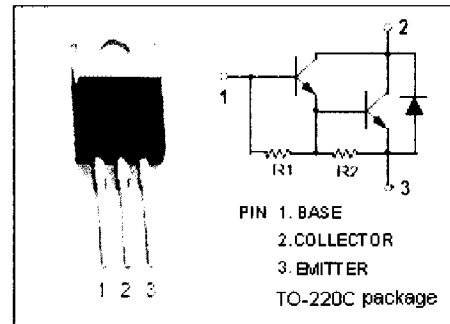
TIP142T

DESCRIPTION

- High DC Current Gain-
 : $h_{FE} = 1000(\text{Min}) @ I_C = 5A$
- Collector-Emitter Sustaining Voltage-
 : $V_{CEO(\text{SUS})} = 100V(\text{Min})$
- Complement to Type TIP147T

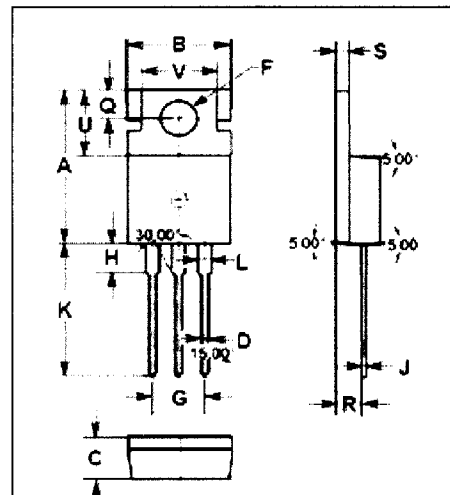
APPLICATIONS

- Designed for general purpose amplifier and low speed switching applications.



ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

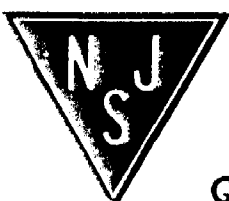
SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current- Continuous	0.5	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	80	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



DIM	mm	
	MIN	MAX
A	15.70	15.90
B	9.90	10.10
C	4.20	4.40
D	0.70	0.90
F	3.40	3.60
G	4.98	5.18
H	2.70	2.90
J	0.44	0.46
K	13.20	13.40
L	1.10	1.30
Q	2.70	2.90
R	2.50	2.70
S	1.29	1.31
U	6.45	6.65
V	8.66	8.86

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.56	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=30\text{mA}, I_B=0$	100			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=5\text{A}, I_B=10\text{mA}$			2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=10\text{A}, I_B=40\text{mA}$			3.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=10\text{A}, I_B=40\text{mA}$			3.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=10\text{A}; V_{CE}=4\text{V}$			3.0	V
I_{CBO}	Collector Cutoff current	$V_{CB}=100\text{V}, I_E=0$			1	mA
I_{CEO}	Collector Cutoff current	$V_{CE}=50\text{V}, I_B=0$			2	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			2	mA
h_{FE-1}	DC Current Gain	$I_C=5\text{A}; V_{CE}=4\text{V}$	1000			
h_{FE-2}	DC Current Gain	$I_C=10\text{A}; V_{CE}=4\text{V}$	500			

Switching Times

t_d	Delay Time	$V_{CC}=30\text{V}, I_C=5.0\text{A}, I_{B1}=-I_{B2}=20\text{mA}; t_p=20\mu\text{s}$ Duty Cycle $\leq 20\%$		0.15		μs
t_r	Rise Time			0.55		μs
t_{stg}	Storage Time			2.5		μs
t_f	Fall Time			2.5		μs